

## Product Summary

BV <sub>DSS</sub>	R <sub>DS(on)</sub> max	I <sub>D</sub> T <sub>A</sub> = +25°C
-40V	60mΩ @ V <sub>GS</sub> = -10V	-6.4A
	100mΩ @ V <sub>GS</sub> = -4.5V	-5.0A

## Description

This new generation MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

## Applications

- DC-DC Converters
- Power Management Functions
- Backlighting

## Features and Benefits

- Low Input Capacitance
- Low On-Resistance
- Fast Switching Speed
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

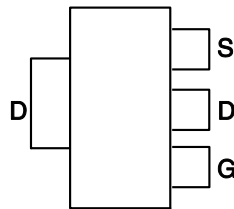
## Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish (63)
- Weight: 0.112 grams (Approximate)

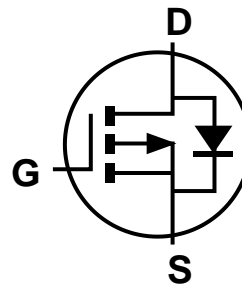
SOT223



Top View



Pin Out - Top



Equivalent Circuit

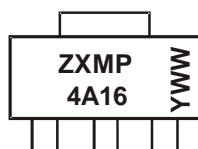
## Ordering Information (Note 4)

Part Number	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXMP4A16GTA	ZXMP4A16	7	12	1,000
ZXMP4A16GTC	ZXMP4A16	13	12	4,000

- Notes:
1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
  2. See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

## Marking Information

SOT223



ZXMP4A16 = Product Type Marking Code  
 YWW = Date Code Marking  
 Y or  $\bar{Y}$  = Last Digit of Year (ex: 5= 2015)  
 WW or  $\bar{W}W$  = Week Code (01~53)

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units
Drain-Source Voltage		V <sub>DSS</sub>	-40	V
Gate-Source Voltage		V <sub>GSS</sub>	±20	V
Continuous Drain Current, V <sub>GS</sub> = -10V	Steady State	T <sub>A</sub> = +25°C (Note 6)	-6.4	A
		T <sub>A</sub> = +70°C (Note 6)	-5.1	
		T <sub>A</sub> = +25°C (Note 5)	-4.6	
Maximum Body Diode Forward Current (Note 6)		I <sub>S</sub>	-5.2	A
Pulsed Drain Current (Note 7)		I <sub>DM</sub>	-21	A
Pulsed Source Current (Note 7)		I <sub>SM</sub>	-21	A

**Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

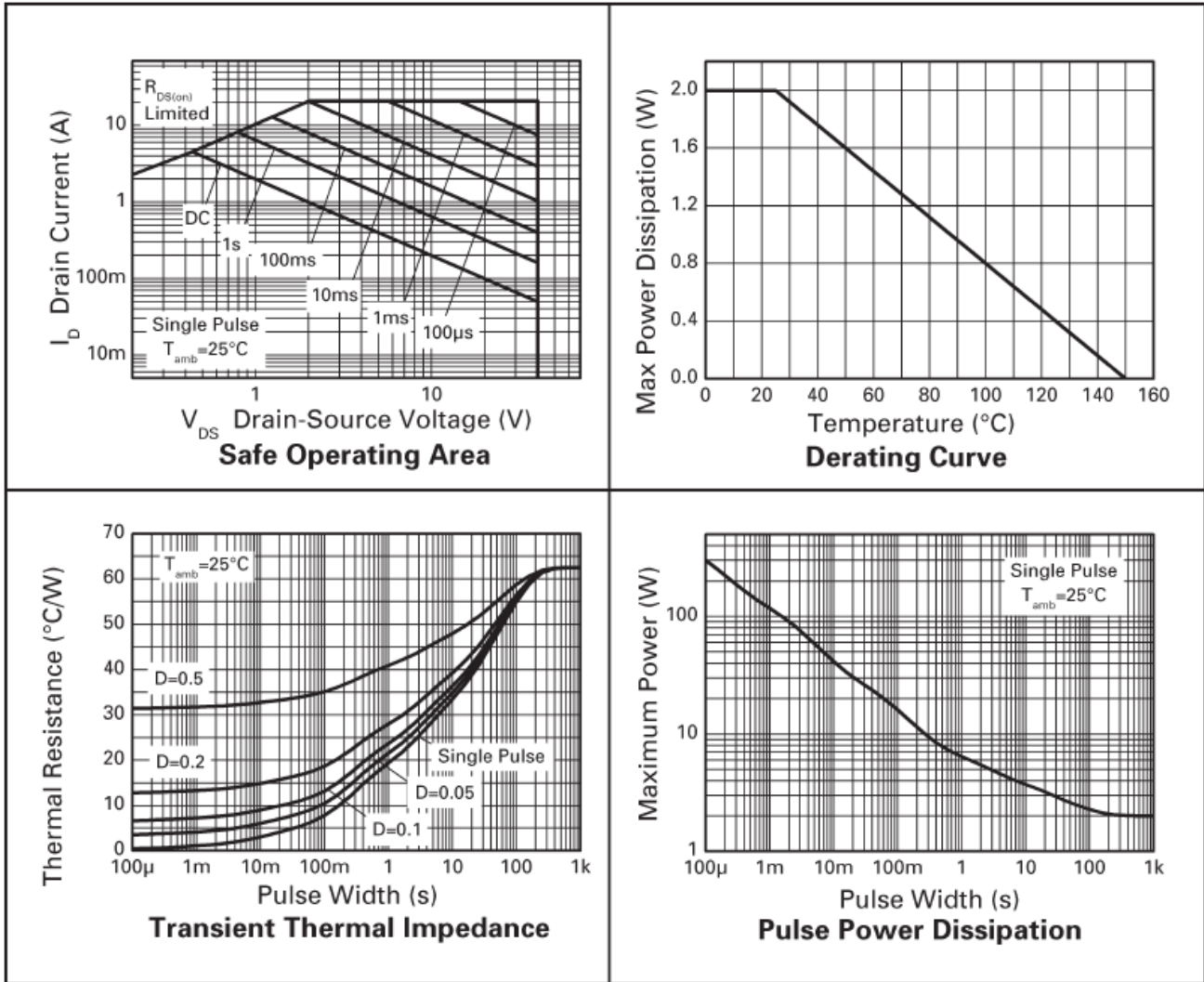
Characteristic		Symbol	Value	Units
Total Power Dissipation	T <sub>A</sub> = +25°C (Note 5)	P <sub>D</sub>	2.0	W
Linear Derating Factor			16	mW/°C
Total Power Dissipation	T <sub>A</sub> = +25°C (Note 6)	P <sub>D</sub>	3.9	W
Linear Derating Factor			31	mW/°C
Thermal Resistance, Junction to Ambient	Steady state (Note 5)	R <sub>θJA</sub>	62.5	°C/W
	Steady state (Note 6)		32	°C/W
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

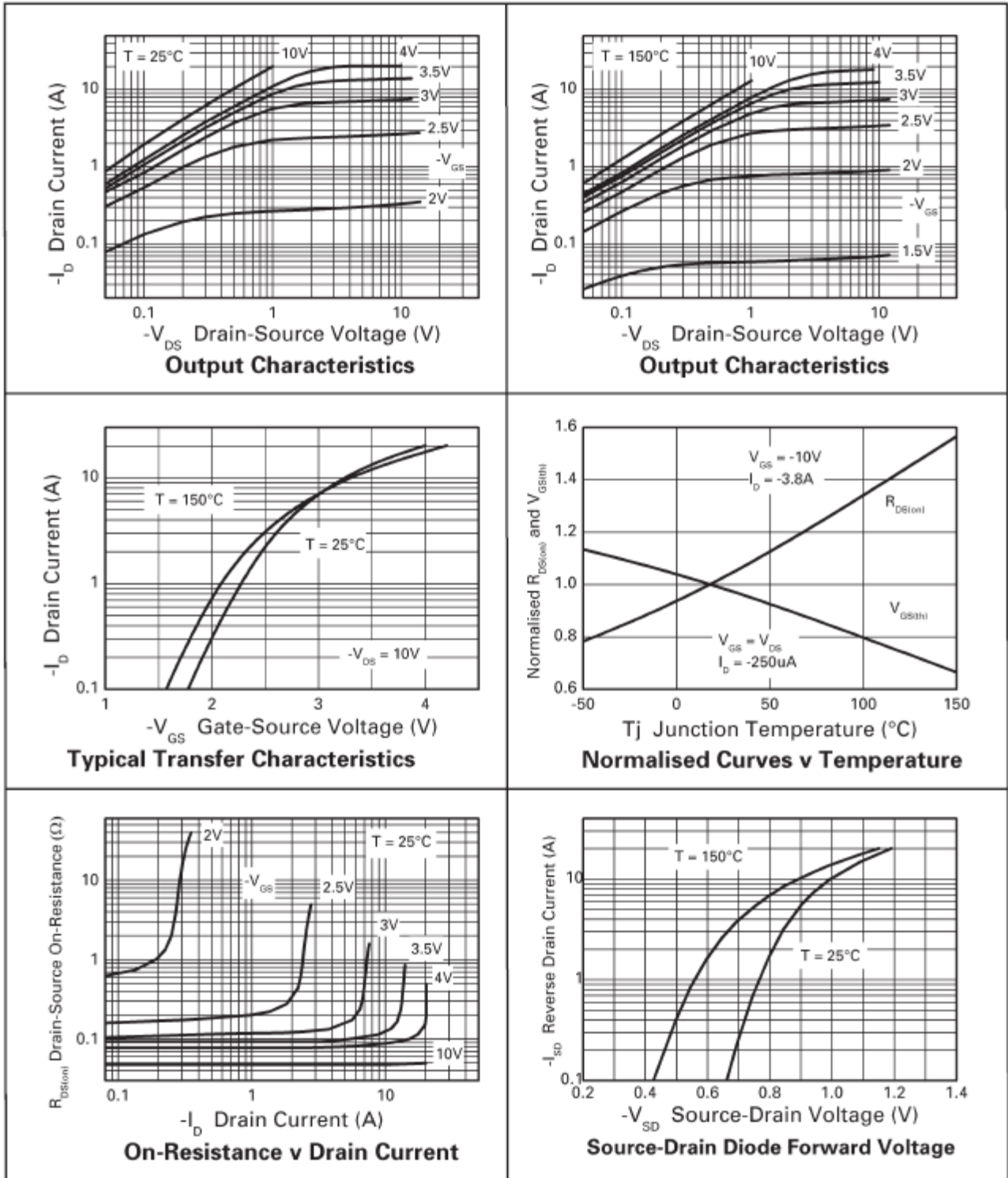
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 9)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-40	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250μA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	-1.0	μA	V <sub>DS</sub> = -40V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 9)</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	-1.0	—	—	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250μA
Static Drain-Source On-Resistance (Note 8)	R <sub>DS(ON)</sub>	—	—	60	mΩ	V <sub>GS</sub> = -10V, I <sub>D</sub> = -3.8A
		—	—	100		V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -2.9A
Diode Forward Voltage (Note 8)	V <sub>SD</sub>	—	-0.85	-1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = -3.4A
Forward Transconductance (Notes 8 & 10)	g <sub>fs</sub>	—	8.85	—	S	V <sub>DS</sub> = -15V, I <sub>D</sub> = -3.8A
<b>DYNAMIC CHARACTERISTICS (Note 10)</b>						
Input Capacitance	C <sub>ISS</sub>	—	1,007	—	pF	V <sub>DS</sub> = -20V, V <sub>GS</sub> = 0V f = 1.0MHz
Output Capacitance	C <sub>OSS</sub>	—	130	—		
Reverse Transfer Capacitance	C <sub>RSS</sub>	—	85	—		
Total Gate Charge (V <sub>GS</sub> = -5.0V)	Q <sub>g</sub>	—	13.6	—	nC	V <sub>DS</sub> = -20V, I <sub>D</sub> = -3.8A,
Total Gate Charge (V <sub>GS</sub> = -10V)	Q <sub>g</sub>	—	26.1	—		
Gate-Source Charge	Q <sub>gs</sub>	—	2.8	—		
Gate-Drain Charge	Q <sub>gd</sub>	—	4.8	—		
Turn-On Delay Time	t <sub>D(on)</sub>	—	2.33	—	nS	V <sub>GS</sub> = -10V, V <sub>DD</sub> = -20V, R <sub>G</sub> = 6.0Ω, I <sub>D</sub> = -1.0A
Turn-On Rise Time	t <sub>r</sub>	—	8.84	—		
Turn-Off Delay Time	t <sub>D(off)</sub>	—	29.18	—		
Turn-Off Fall Time	t <sub>f</sub>	—	12.54	—		
Body Diode Reverse Recovery Time	t <sub>rr</sub>	—	27.2	—	nS	I <sub>F</sub> = -3A, dI/dt = 100A/μs
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>	—	25.4	—	nC	

- Notes:
5. For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.
  6. For a device surface mounted on FR4 PCB measured at t ≤ 10 secs.
  7. Repetitive rating 25mm x 25mm FR4 PCB, D = 0.05, pulse width limited by maximum junction temperature.
  8. Measured under pulsed conditions. Width ≤ 300μs. Duty cycle ≤ 2%.
  9. Short duration pulse test used to minimize self-heating effect.
  10. Guaranteed by design. Not subject to product testing.

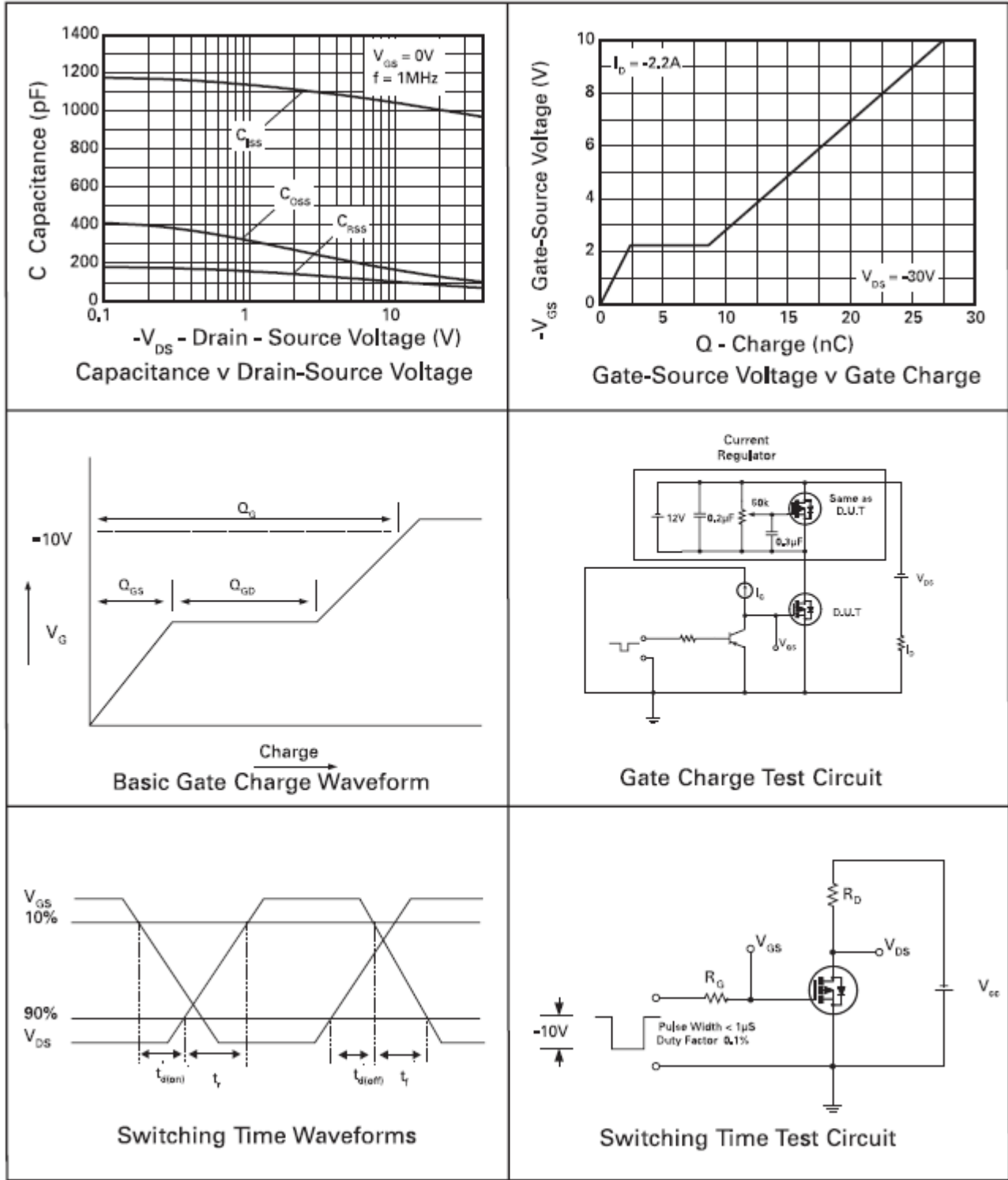
**Typical Characteristics**



**Typical Characteristics** (continued)

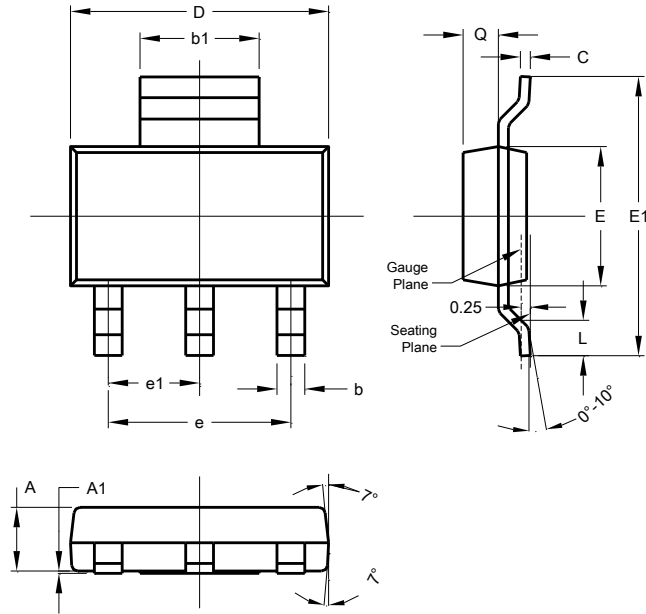


**Typical Characteristics** (continued)



**Package Outline Dimensions**

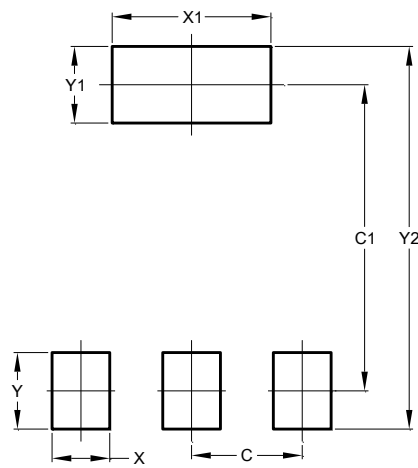
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



SOT223			
Dim	Min	Max	Typ
A	1.55	1.65	1.60
A1	0.010	0.15	0.05
b	0.60	0.80	0.70
b1	2.90	3.10	3.00
C	0.20	0.30	0.25
D	6.45	6.55	6.50
E	3.45	3.55	3.50
E1	6.90	7.10	7.00
e	-	-	4.60
e1	-	-	2.30
L	0.85	1.05	0.95
Q	0.84	0.94	0.89
All Dimensions in mm			

**Suggested Pad Layout**

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
C	2.30
C1	6.40
X	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00

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